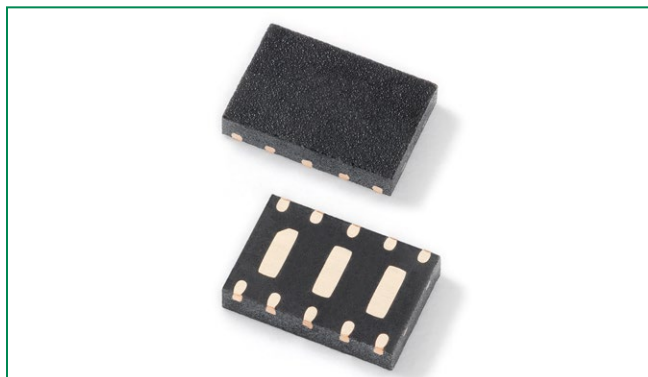


SP2555NUTG 2.5V 45A Diode Array

HF RoHS  GREEN

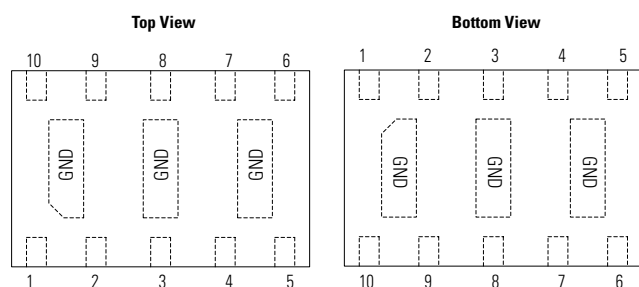


Description

The SP2555NUTG is a low-capacitance, TVS Diode Array designed to provide protection against ESD (electrostatic discharge), CDE (cable discharge events), EFT (electrical fast transients), and lightning induced surges for high-speed, differential data lines. It's packaged in a μ DFN package (3.0 x 2.0mm) and each component can protect up to 4 channels or 2 differential pairs, up to 45A (IEC 61000-4-5 2nd edition,) and up to 30kV ESD (IEC 61000-4-2). The "flow-through" design minimizes signal distortion, reduces voltage overshoot, and provides a simplified PCB design.

The SP2555NUTG with its low capacitance and low clamping voltage makes it ideal for high-speed data interfaces such as 1GbE applications found in notebooks, switches, etc.

Pinout

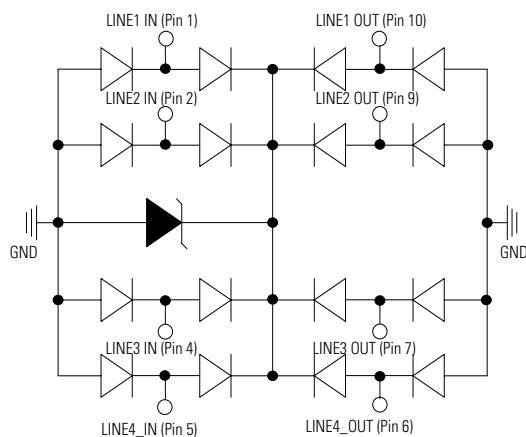


NOTE: PIN3, PIN8 are same potential with GND

Features

- ESD, IEC 61000-4-2, ± 30 kV contact, ± 30 kV air
- EFT, IEC 61000-4-4, 40A (5/50ns)
- Lightning, 45A (8/20 μ s as defined in IEC 61000-4-5 2nd Edition)
- Low capacitance of 2.5pF@0V (TYP) per I/O
- Low leakage current of 0.1 μ A (TYP) at 2.5V
- μ DFN-10 package is optimized for high-speed data line routing
- Provides protection for two differential data pairs (4 channels) up to 45A
- Low operating and clamping voltage
- AEC-Q101 qualified
- Halogen free, Lead free and RoHS compliant

Functional Block Diagram



Life Support Note:

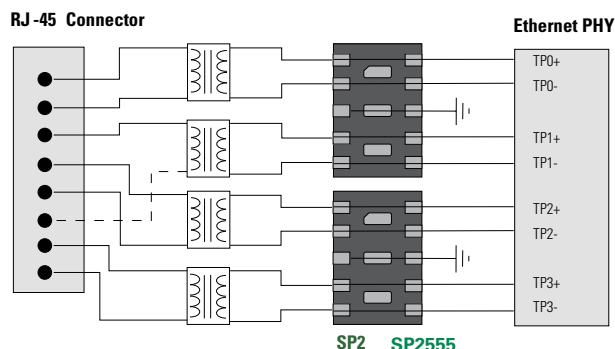
Not Intended for Use in Life Support or Life Saving Applications

The products shown herein are not designed for use in life sustaining or life saving applications unless otherwise expressly indicated.

Applications

- 10/100/1000 Ethernet
- WAN/LAN Equipment
- Desktops, Servers and Notebooks
- LVDS Interfaces
- Integrated Magnetics
- Smart TV

Application Example



Absolute Maximum Ratings

Symbol	Parameter	Value	Units
I_{PP}	Peak Current ($t_p=8/20\mu s$)	45	A
P_{PK}	Peak Pulse Power ($t_p=8/20\mu s$)	1000	W
T_{OP}	Operating Temperature	-40 to 125	°C
T_{STOR}	Storage Temperature	-55 to 150	°C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the component. This is a stress only rating and operation of the component at these or any other conditions above those indicated in the operational sections of this specification is not implied.

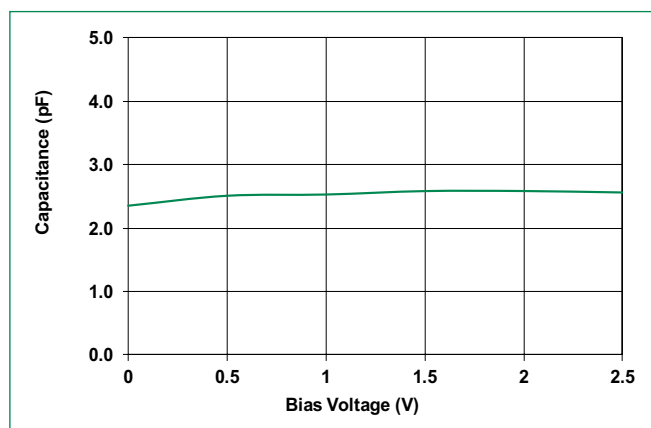
Electrical Characteristics ($T_{OP}=25^{\circ}C$)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Reverse Standoff Voltage	V_{RWM}	$I_R \leq 1\mu A$			2.5	V
Reverse Leakage Current	I_R	$V_{RWM} = 2.5V, T = 25^{\circ}C$		0.1	0.5	μA
Snap Back Voltage	V_{SB}	$I_{SB} = 50mA$	2.0			V
Clamp Voltage	V_C	$I_{PP} = 1A, t_p = 8/20\mu s$, Any I/O to Ground		4.5		V
		$I_{PP} = 10A, t_p = 8/20\mu s$, Any I/O to Ground		7.5		
		$I_{PP} = 25A, t_p = 8/20\mu s$, Any I/O to Ground		12		
		$I_{PP} = 45A, t_p = 8/20\mu s$, Line-to-Line ¹ , two I/O Pins connected together on each line		19		
Dynamic Resistance ²	R_{DYN}	TLP, $t_p=100ns$, Any I/O to Ground		0.1		Ω
ESD Withstand Voltage	V_{ESD}	IEC 61000-4-2 (Contact)	± 30			kV
		IEC 61000-4-2 (Air)	± 30			kV
Diode Capacitance	$C_{I/O \text{ to GND}}$	Between I/O Pins and Ground $V_p = 0V, f = 1MHz$		2.5		pF
	$C_{I/O \text{ to I/O}}$	Between I/O Pins $V_p = 0V, f = 1MHz$		1.2		pF

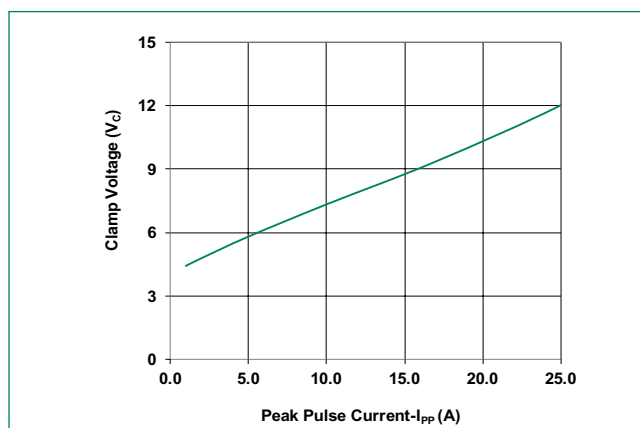
Notes:

- Rating with 2 pins connected together per suggested diagram (For example, pin1 is connected to pin 10, pin 2 is connected to Pin 9, Pin 4 is connected to pin 7 and pin 5 is connected to pin 6)
- Transmission Line Pulse (TLP) with 100ns width, 2ns rise time, and average window $t_1=70ns$ to $t_2=90ns$

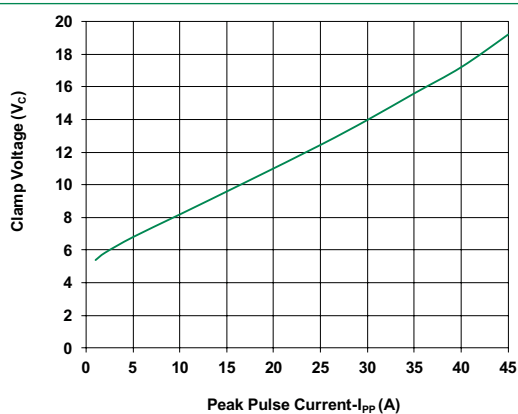
Capacitance vs. Reverse Bias



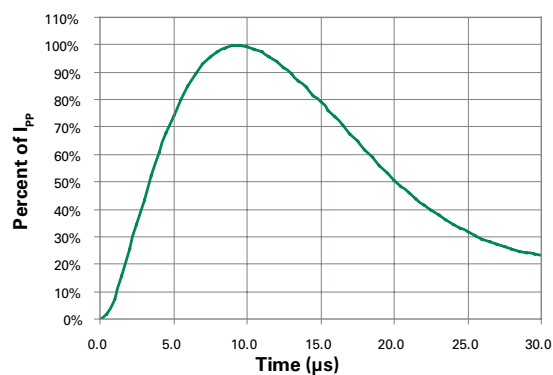
Clamping Voltage vs. I_{PP} (I/O to GND)



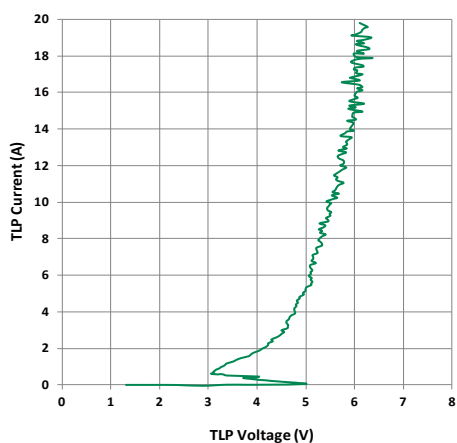
Clamping Voltage vs. I_{pp} (Line-to-Line)



8/20 μ s Pulse Waveform

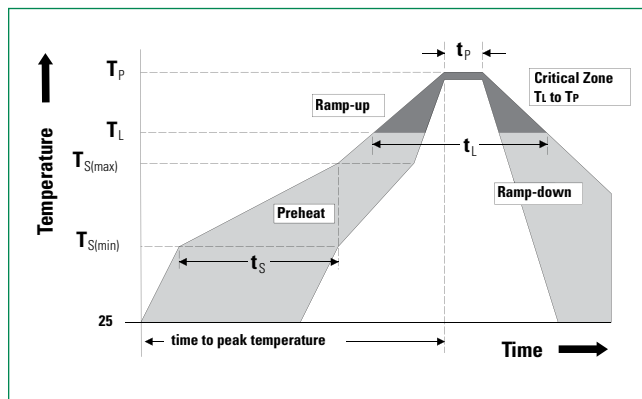


Transmission Line Pulsing (TLP) Plot



Soldering Parameters

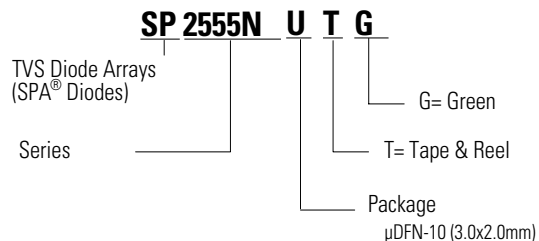
Reflow Condition		Pb – Free assembly
Pre Heat	-Temperature Min ($T_{s(min)}$)	150°C
	-Temperature Max ($T_{s(max)}$)	200°C
	-Time (min to max) (t_s)	60 – 180 secs
Average ramp up rate (Liquidus) Temp (T_L) to peak		3°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/second max
Reflow	-Temperature (T_L) (Liquidus)	217°C
	-Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_p)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		6°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		260°C



Ordering Information

Part Number	Package	Min. Order Qty.
SP2555NUTG	μDFN-10 (3.0x2.0mm)	3000

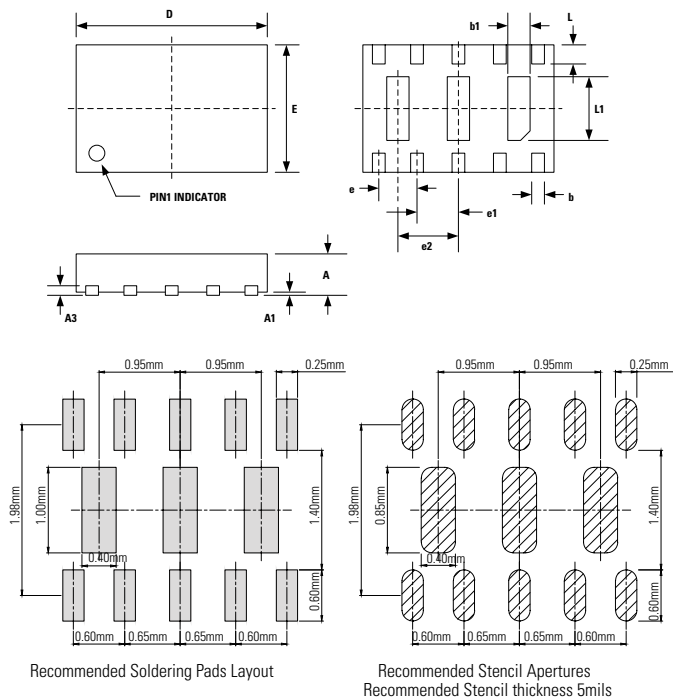
Part Numbering System



Part Marking System



Package Dimensions — μ DFN-10 (3.0x2.0mm)

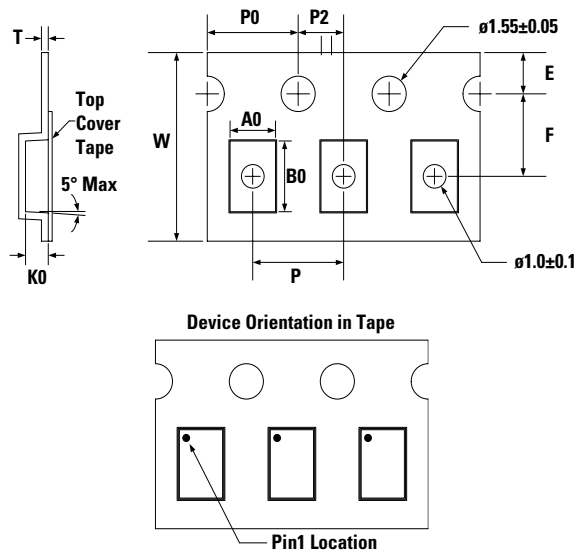


Package	μ DFN-10 (3.0x2.0mm)					
JEDEC	MO-229					
Symbol	Millimeters			Inches		
	Min	Nom	Max	Min	Nom	Max
A	0.50	0.60	0.65	0.020	0.024	0.026
A1	0.00	0.03	0.05	0.000	0.001	0.002
A3	0.15 Ref			0.006 Ref		
b	0.15	0.20	0.25	0.006	0.008	0.010
b1	0.25	0.35	0.45	0.010	0.014	0.018
D	2.90	3.00	3.10	0.114	0.118	0.122
E	1.90	2.00	2.10	0.075	0.079	0.083
e	0.60 BSC			0.024 BSC		
e1	0.65 BSC			0.026 BSC		
e2	0.95 BSC			0.037		
L	0.25	0.30	0.35	0.010	0.012	0.014
L1	0.95	1.00	1.05	0.037	0.039	0.041

Notes :

1. All dimensions are in millimeters
2. Dimensions include solder plating.
3. Dimensions are exclusive of mold flash & metal burr

Tape & Reel Specification — μ DFN-10 (3.0x2.0mm)



Package	μ DFN-10 (3.0x2.0mm)
Symbol	Millimeters
A0	2.30 +/- 0.10
B0	3.20 +/- 0.10
E	1.75 +/- 0.10
F	3.50 +/- 0.05
K0	1.0 +/- 0.10
P	4.00 +/- 0.10
P0	4.00 +/- 0.10
P2	2.00 +/- 0.10
T	0.3 +/- 0.05
W	8.00 +0.30/- 0.10

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9